

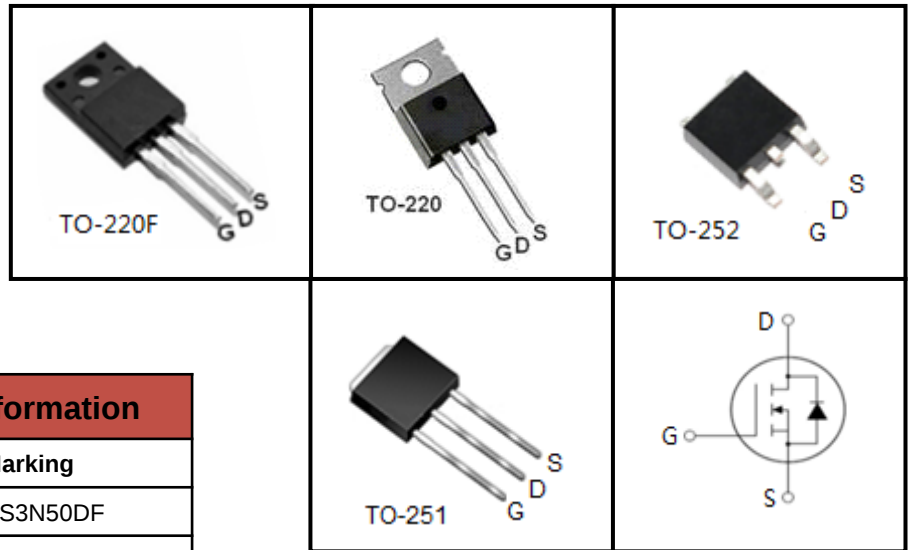
500V N-Channel MOSFET

FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)



Device Marking and Package Information

Device	Package	Marking
CS3N50DF	TO-220F	CS3N50DF
CS3N50DP	TO-220	CS3N50DP
CS3N50DD	TO-252	CS3N50DD
CS3N50DU	TO-251	CS3N50DU

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value				Unit
		TO-220F	TO-220	TO-251	TO-252	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	500				V
Continuous Drain Current	I _D	3				A
Pulsed Drain Current (note1)	I _{DM}	12				A
Gate-Source Voltage	V _{GSS}	±30				V
Single Pulse Avalanche Energy (note2)	E _{AS}	60				mJ
Avalanche Current (note1)	I _{AR}	3.4				A
Repetitive Avalanche Energy (note1)	E _{AR}	36				mJ
Power Dissipation (T _C = 25°C)	P _D	45	30			W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150				°C

Thermal Resistance

Parameter	Symbol	Value				Unit
		TO-220F	TO-220	TO-251	TO-252	
Thermal Resistance, Junction-to-Case	R _{thJC}	5	1.78			K/W
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60			

Specifications $T_J = 25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	500	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 500V, V _{GS} = 0V, T _J = 25°C	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±30V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	3	--	4	V
Drain-Source On-Resistance (Note3)	R _{DS(on)}	V _{GS} = 10V, I _D =1.5A	--	2.4	3	Ω
Dynamic						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1.0MHz	--	293	--	pF
Output Capacitance	C _{oss}		--	32	--	
Reverse Transfer Capacitance	C _{rss}		--	2.5	--	
Total Gate Charge	Q _g	V _{DD} = 400V, I _D = 3A, V _{GS} = 10V	--	9.6	--	nC
Gate-Source Charge	Q _{gs}		--	1.6	--	
Gate-Drain Charge	Q _{gd}		--	4.8	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 250V, I _D = 3A, R _G = 25 Ω	--	33	--	ns
Turn-on Rise Time	t _r		--	5.3	--	
Turn-off Delay Time	t _{d(off)}		--	57	--	
Turn-off Fall Time	t _f		--	34	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25 °C	--	--	3	A
Pulsed Diode Forward Current	I _{SM}		--	--	12	
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 1.5A, V _{GS} = 0V	--	--	1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} = 0V,I _S = 3A, di _F /dt =100A /μs	--	425	--	ns
Reverse Recovery Charge	Q _{rr}		--	784	--	nC

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L=10mH, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 1\%$

Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics ($T_J = 25^\circ\text{C}$)

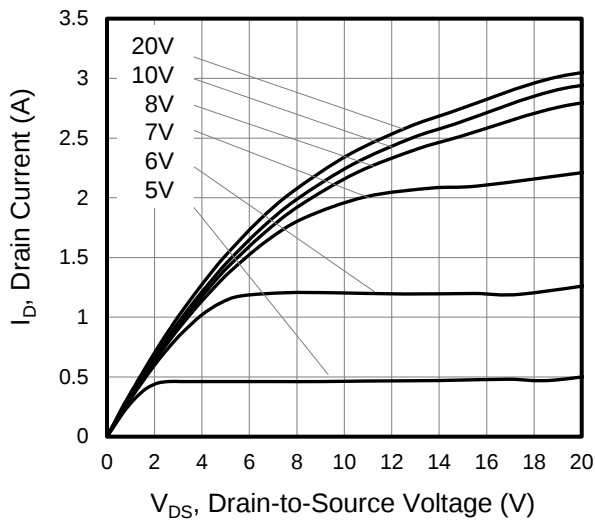


Figure 2. Body Diode Forward Voltage

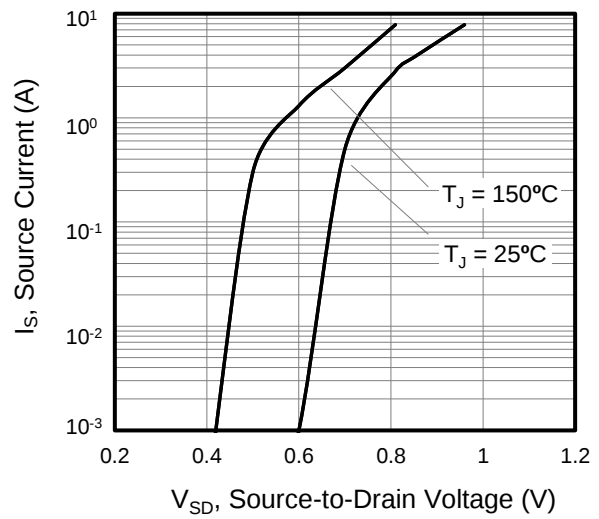


Figure 3. Drain Current vs. Temperature

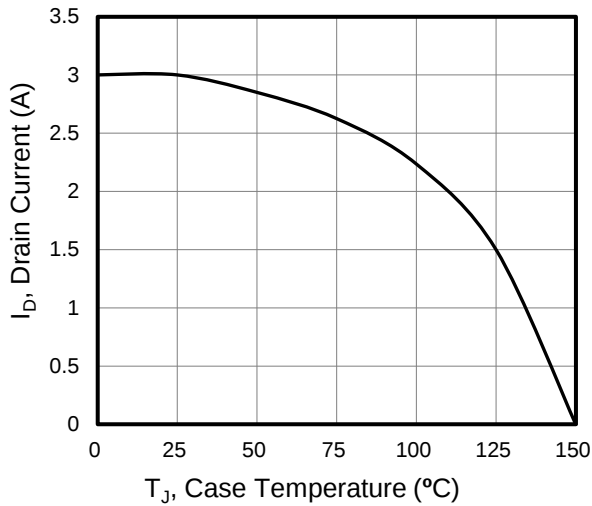


Figure 4. BV_{DSS} Variation vs. Temperature

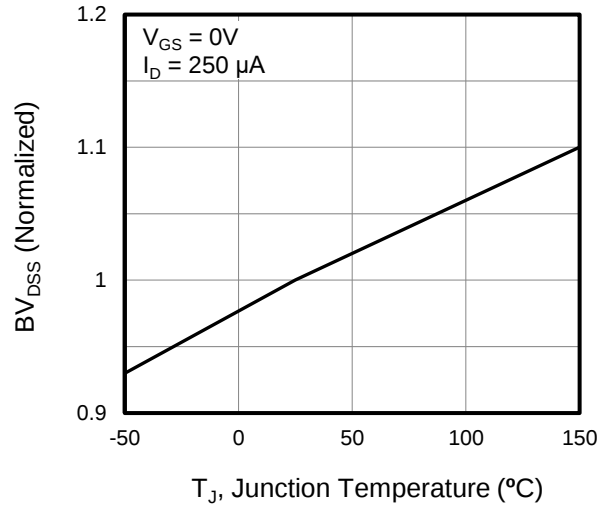


Figure 5. Transfer Characteristics

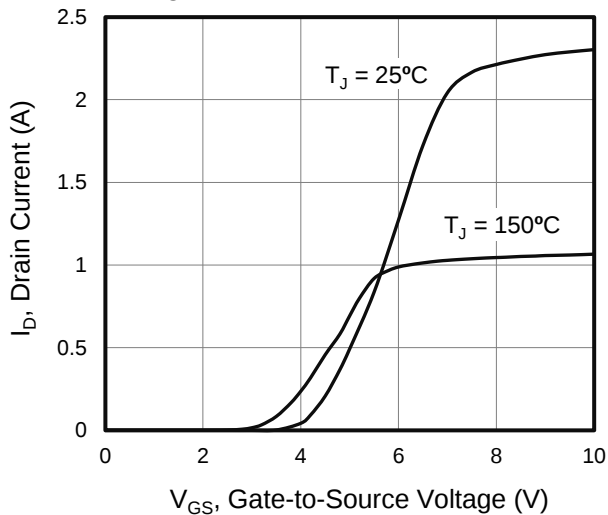
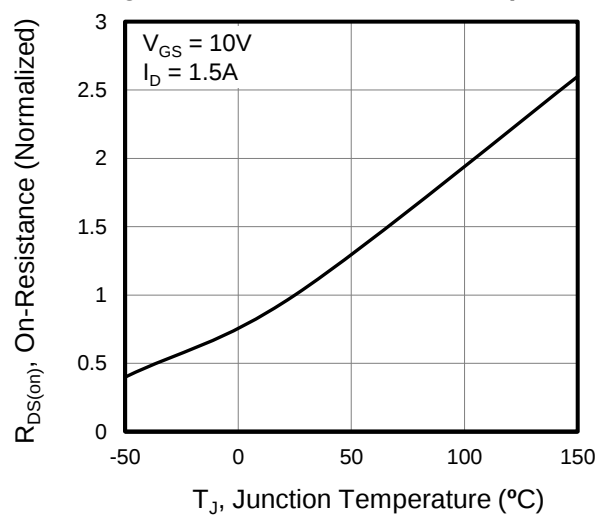


Figure 6. On-Resistance vs. Temperature



Typical Characteristics $T_j = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Capacitance

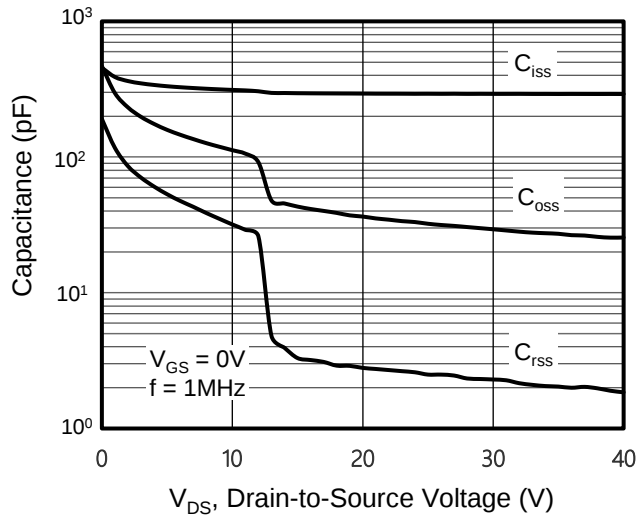


Figure 8. Gate Charge

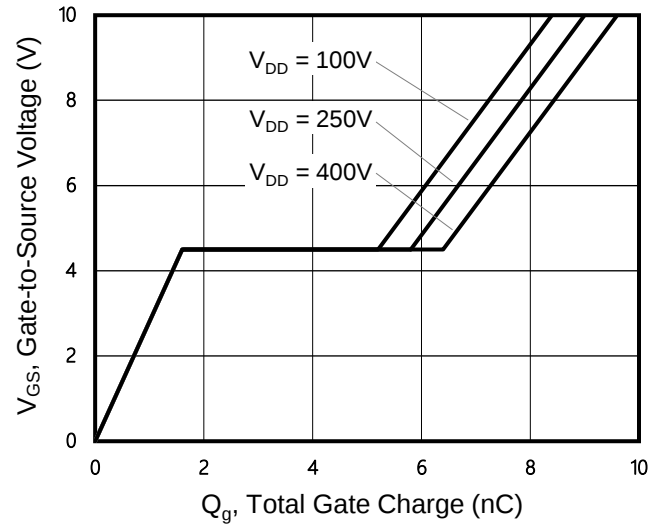


Figure 9. Transient Thermal Impedance

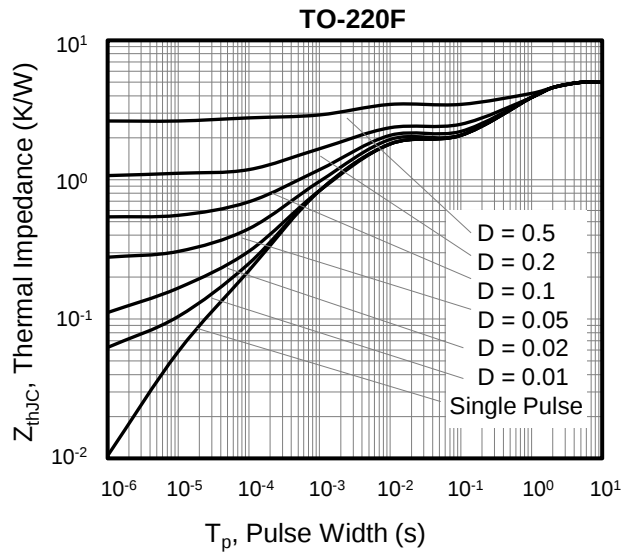


Figure 10. Transient Thermal Impedance

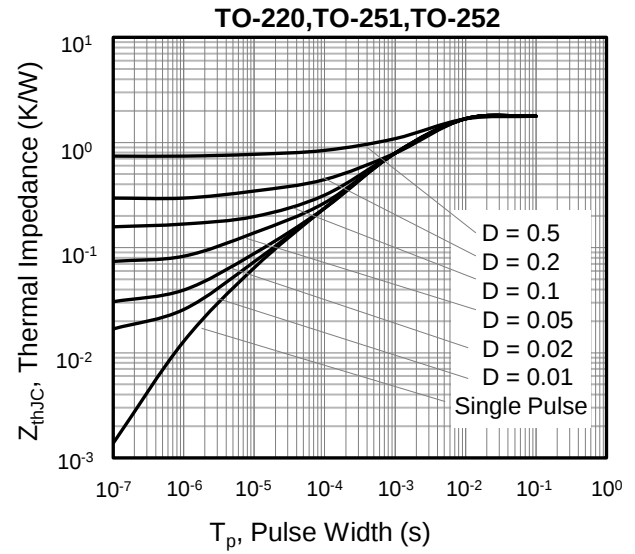


Figure A: Gate Charge Test Circuit and Waveform

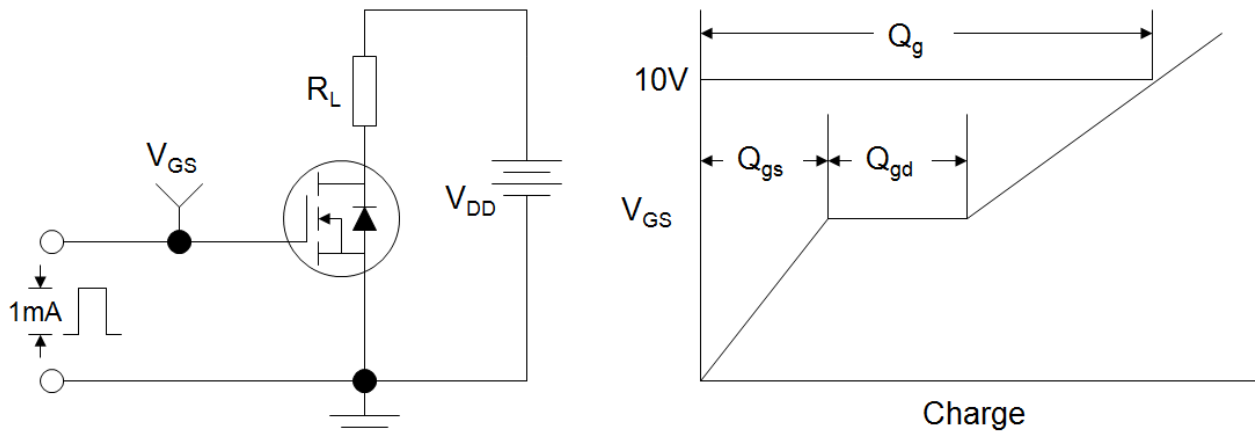
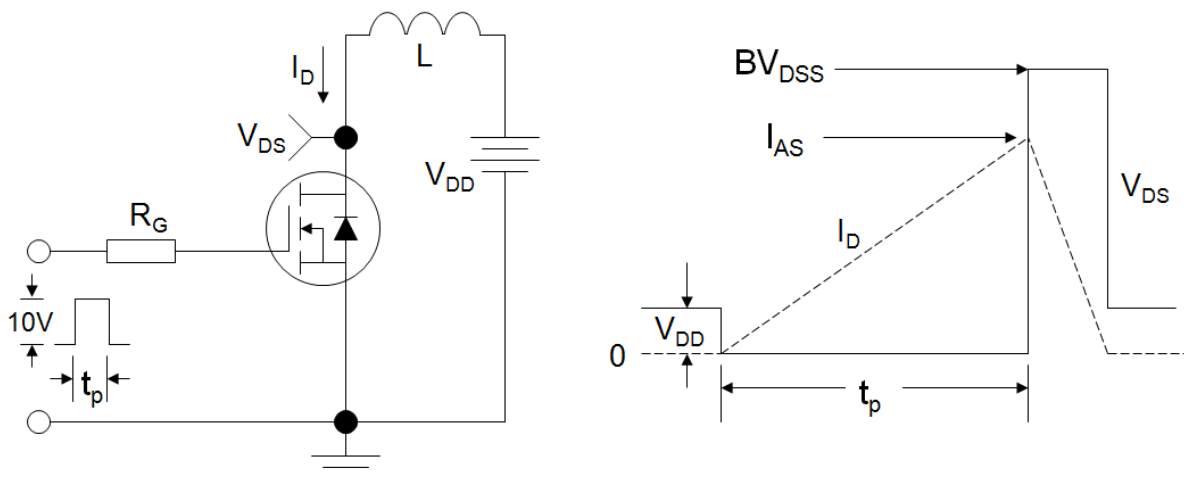


Figure B: Resistive Switching Test Circuit and Waveform



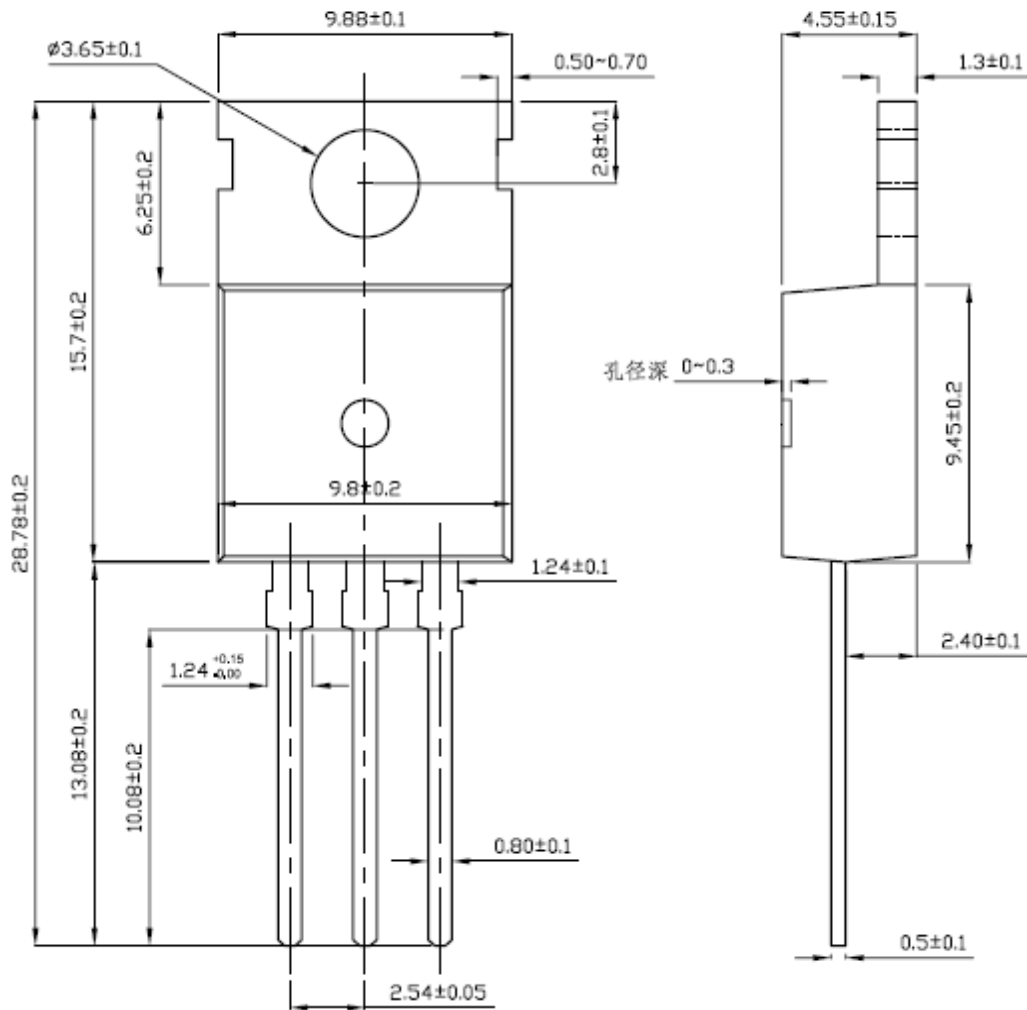
Figure C: Unclamped Inductive Switching Test Circuit and Waveform



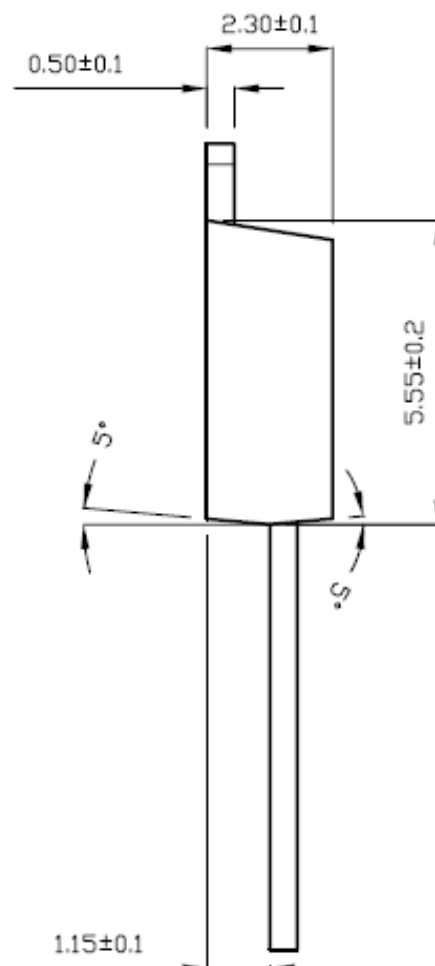
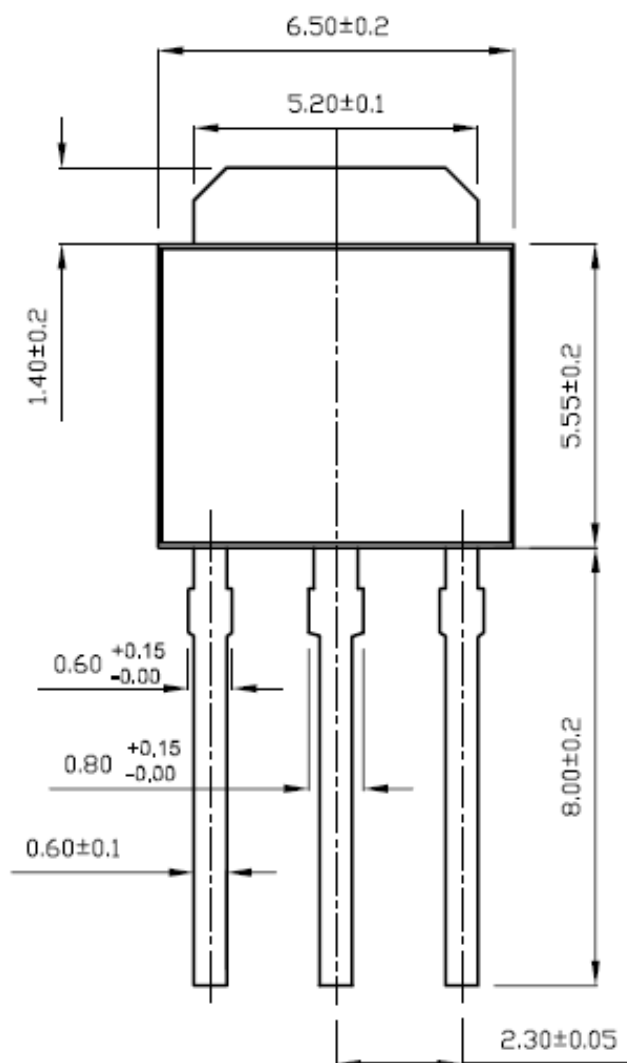
TO-220F



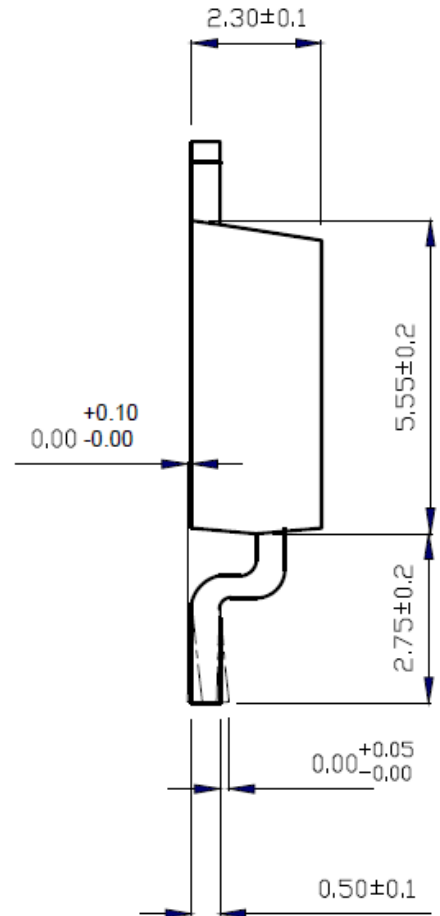
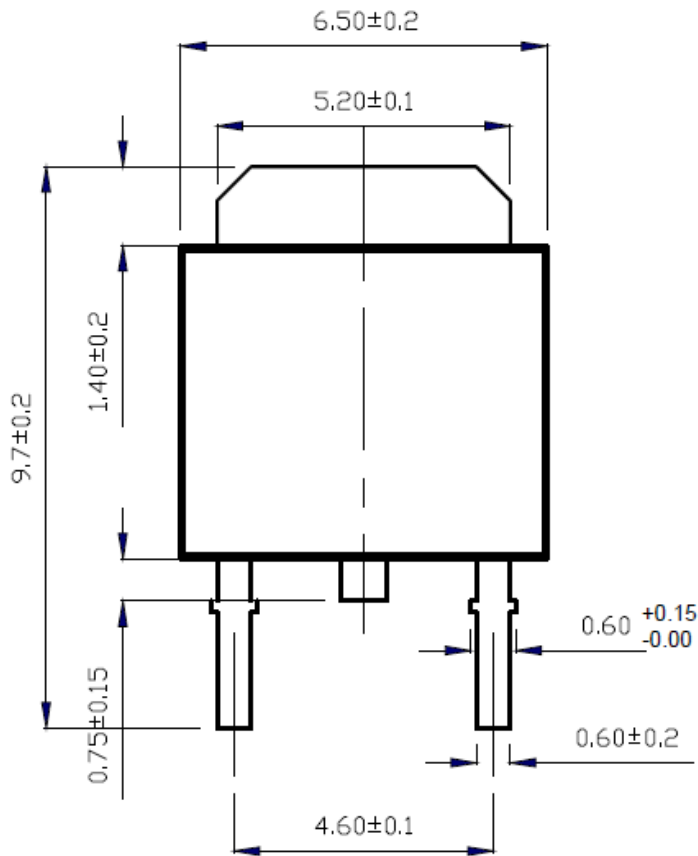
TO-220



TO-251



TO-252



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